

MOSFET – Power, N-Channel, SUPERFET III, FRFET

650 V, 20 A, 190 mΩ

NTP190N65S3HF

Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET is very suitable for the various power system for miniaturization and higher efficiency.

SUPERFET III FRFET MOSFET's optimized reverse recovery performance of body diode can remove additional component and improve system reliability.

Features

- 700 V @ $T_J = 150^{\circ}\text{C}$
- Typ. $R_{DS(on)} = 159\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 34\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 316\text{ pF}$)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

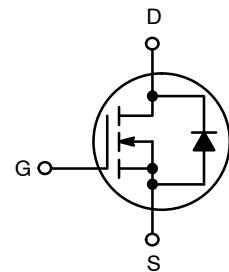
- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter



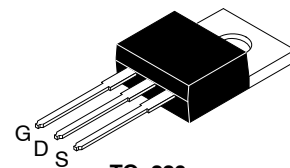
ON Semiconductor®

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V_{DS}	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
650 V	190 mΩ @ 10 V	20 A

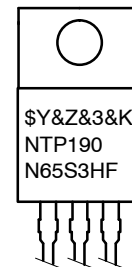


POWER MOSFET



**TO-220
CASE 340AT**

MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Data Code (Year & Week)
&K	= Lot
NTP190N65S3HF	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NTP190N65S3HF

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{DSS}	Drain to Source Voltage		650	V
V _{GSS}	Gate to Source Voltage	– DC	±30	V
		– AC (f > 1 Hz)	±30	
I _D	Drain Current	– Continuous (T _C = 25°C)	20	A
		– Continuous (T _C = 100°C)	12.7	
I _{DM}	Drain Current	– Pulsed (Note 1)	50	A
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		220	mJ
I _{AS}	Avalanche Current (Note 2)		3.7	A
E _{AR}	Repetitive Avalanche Energy (Note 1)		1.62	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		50	
P _D	Power Dissipation	(T _C = 25°C)	162	W
		– Derate Above 25°C	1.3	
T _J , T _{STG}	Operating and Storage Temperature Range		–55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 3.7 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 10 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max.	0.77	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient, Max.	62.5	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NTP190N65S3HF	NTP190N65S3HF	TO-220	Tube	N/A	N/A	50 Units

NTP190N65S3HF

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 1 mA, T _J = 25°C	650			V
		V _{GS} = 0 V, I _D = 1 mA, T _J = 150°C	700			V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 10 mA, Referenced to 25°C		0.65		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650 V, V _{GS} = 0 V			10	μA
		V _{DS} = 520 V, T _C = 125°C		65		
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V			±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 0.43 mA	3.0		5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 10 A		159	190	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 10 A		11		S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 400 V, V _{GS} = 0 V, f = 1 MHz		1610		pF
C _{oss}	Output Capacitance			30		pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		316		pF
C _{oss(er.)}	Energy Related Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		59		pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 400 V, I _D = 10 A, V _{GS} = 10 V (Note 4)		34		nC
Q _{gs}	Gate to Source Gate Charge			11		nC
Q _{gd}	Gate to Drain "Miller" Charge			13		nC
ESR	Equivalent Series Resistance	f = 1 MHz		6.8		Ω

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	V _{DD} = 400 V, I _D = 10 A, V _{GS} = 10 V, R _g = 4.7 Ω (Note 4)		19		ns
t _r	Turn-On Rise Time			19		ns
t _{d(off)}	Turn-Off Delay Time			58		ns
t _f	Turn-Off Fall Time			14		ns

SOURCE-DRAIN DIODE CHARACTERISTICS

I _S	Maximum Continuous Source to Drain Diode Forward Current			20	A
I _{SM}	Maximum Pulsed Source to Drain Diode Forward Current			50	A
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 10 A		1.3	V
t _{rr}	Reverse Recovery Time	V _{DD} = 400 V, I _{SD} = 10 A, dI _F /dt = 100 A/μs		80	ns
Q _{rr}	Reverse Recovery Charge			264	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL CHARACTERISTICS

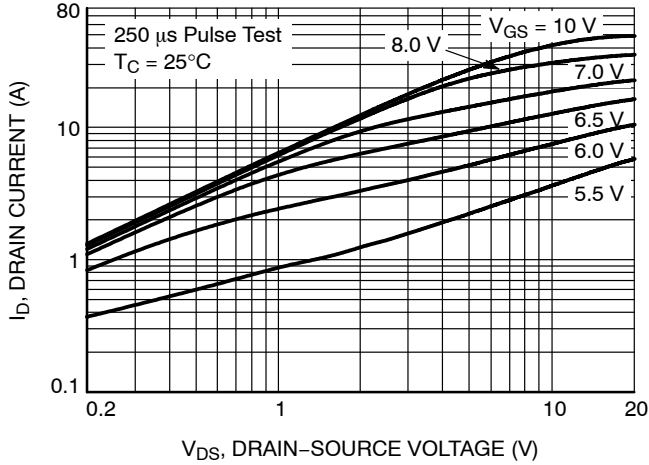


Figure 1. On-Region Characteristics

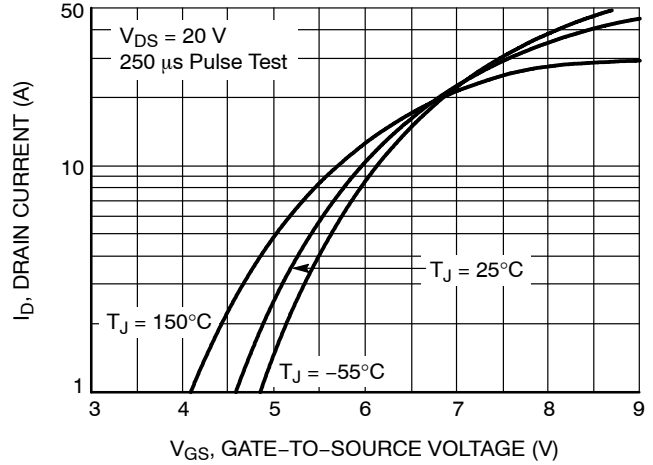


Figure 2. Transfer Characteristics

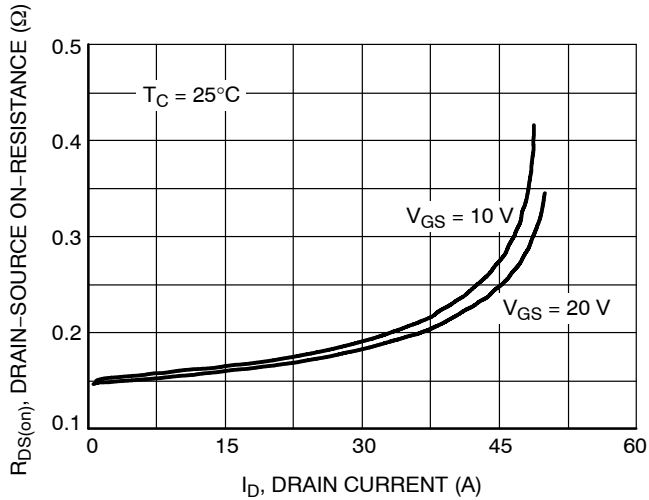


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

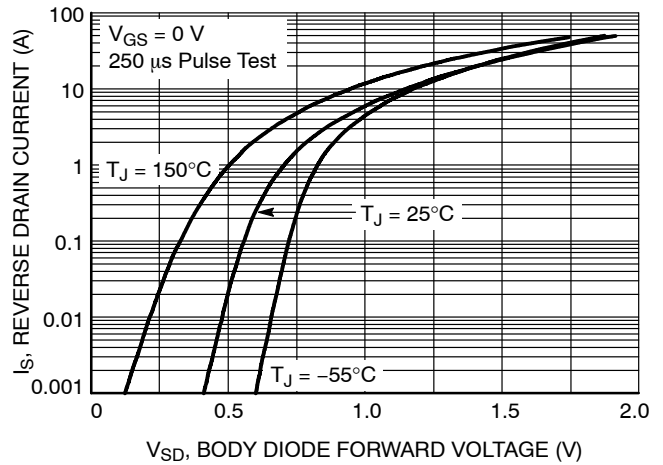


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

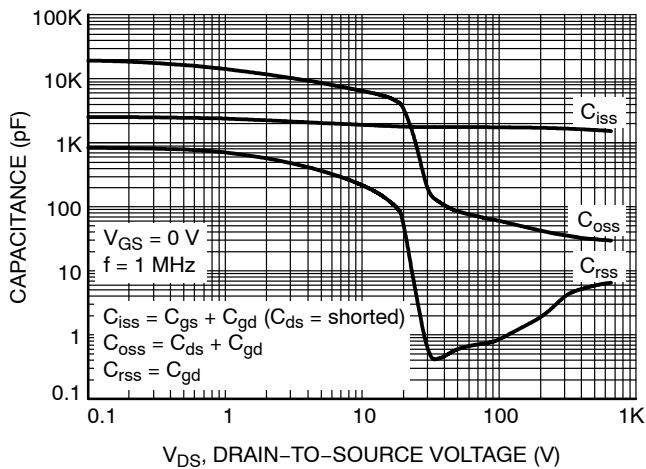


Figure 5. Capacitance Characteristics

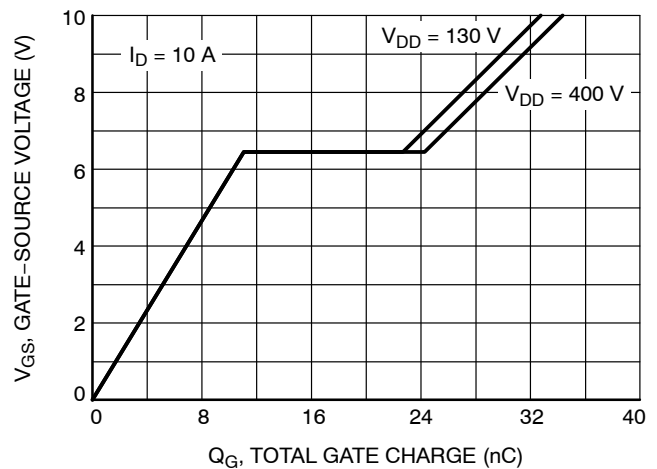


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS

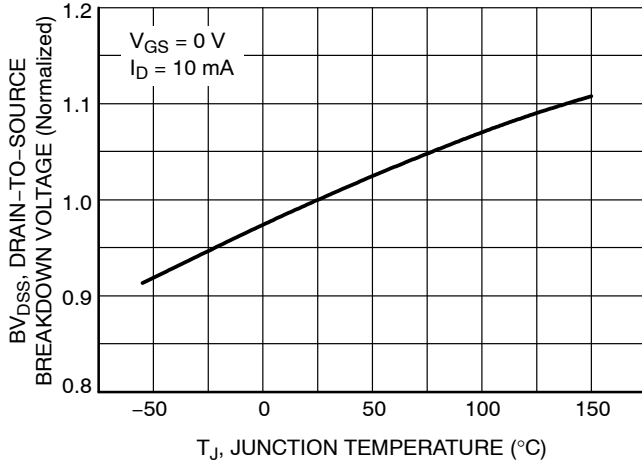


Figure 7. Breakdown Voltage Variation vs. Temperature

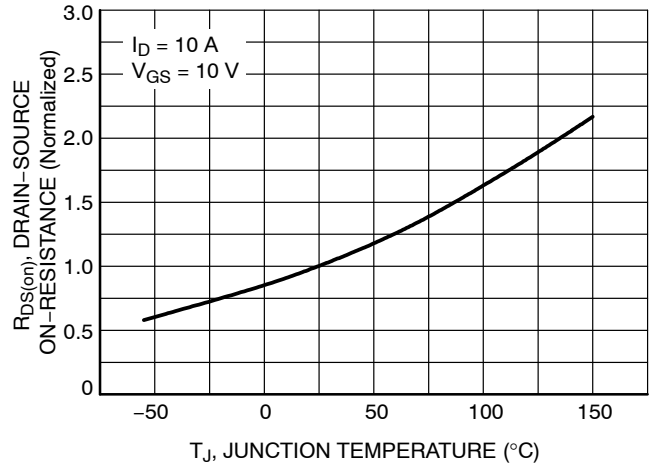


Figure 8. On-Resistance Variation vs. Temperature

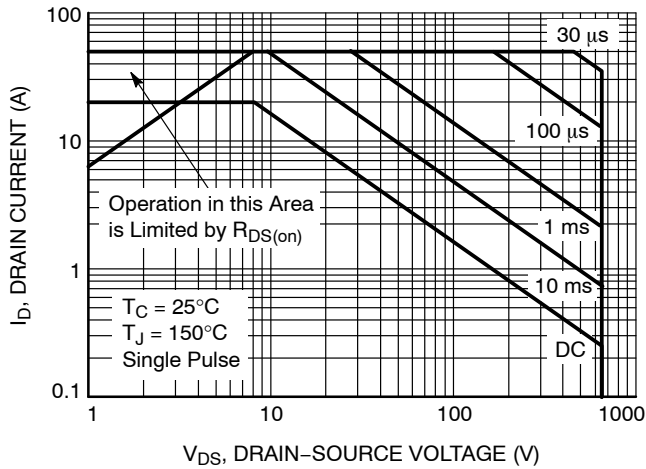


Figure 9. Maximum Safe Operating Area

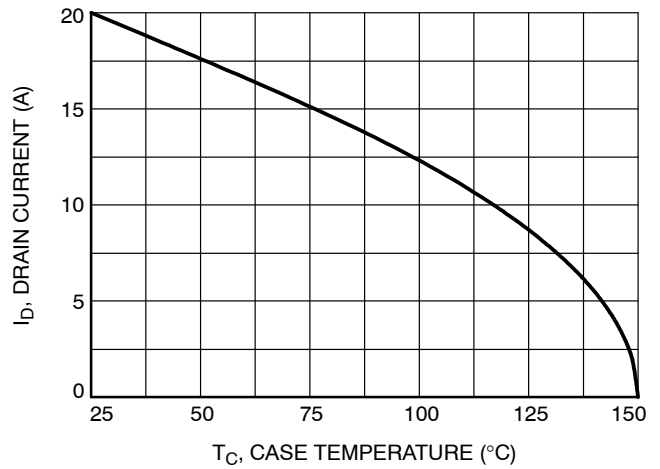


Figure 10. Maximum Drain Current vs. Case Temperature

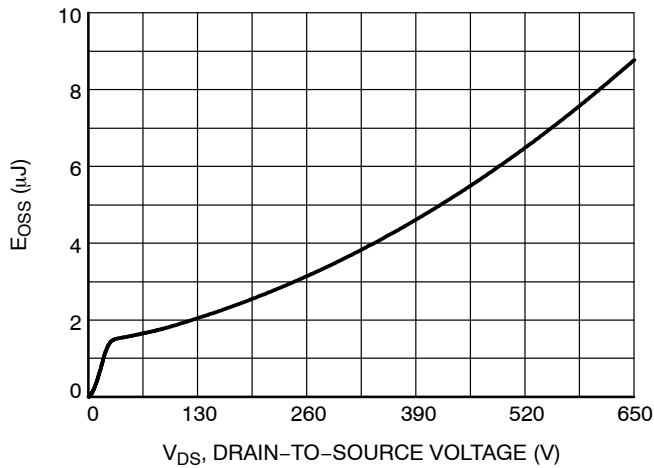


Figure 11. E_{OSS} vs. Drain-to-Source Voltage

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TYPICAL CHARACTERISTICS

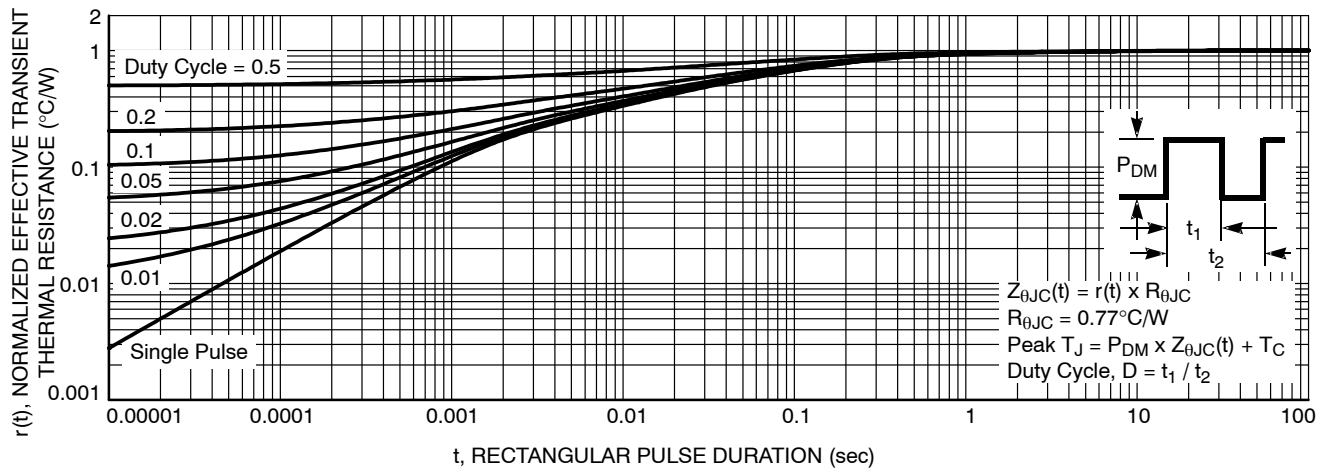


Figure 12. Transient Thermal Response Curve

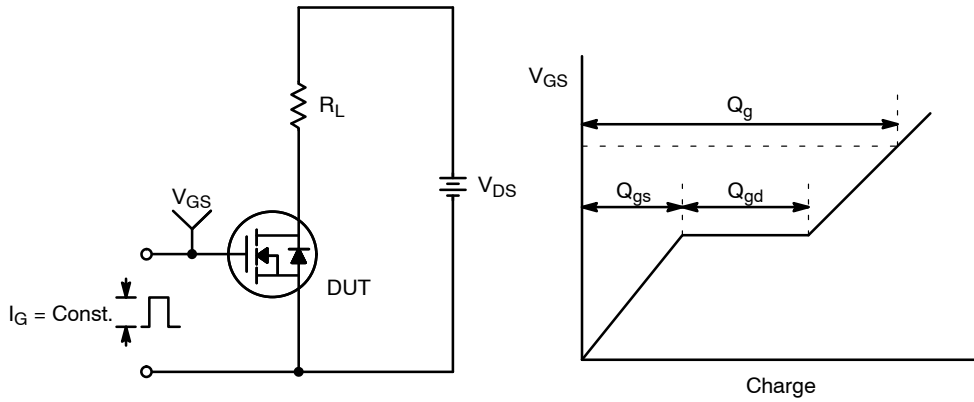


Figure 13. Gate Charge Test Circuit & Waveform

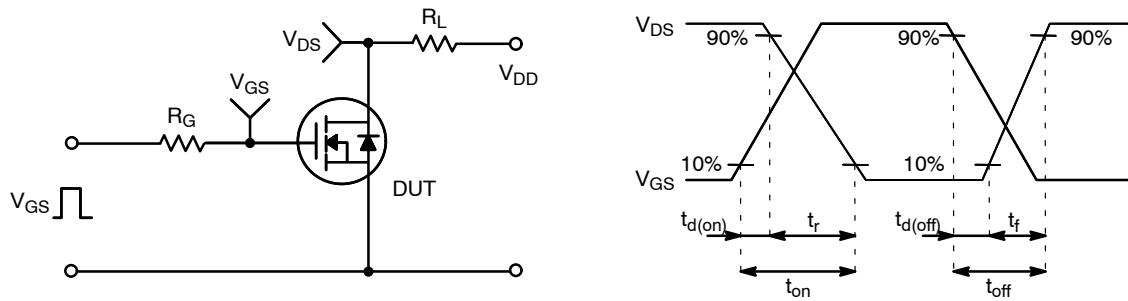


Figure 14. Resistive Switching Test Circuit & Waveforms

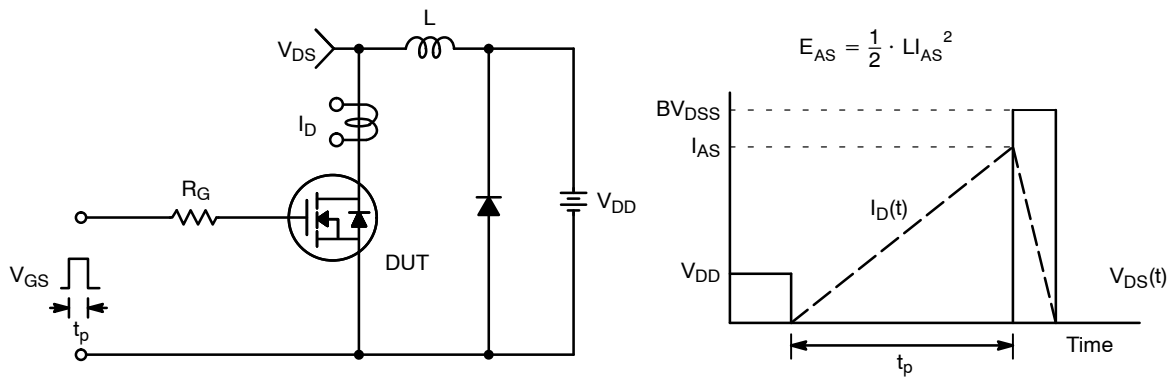


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

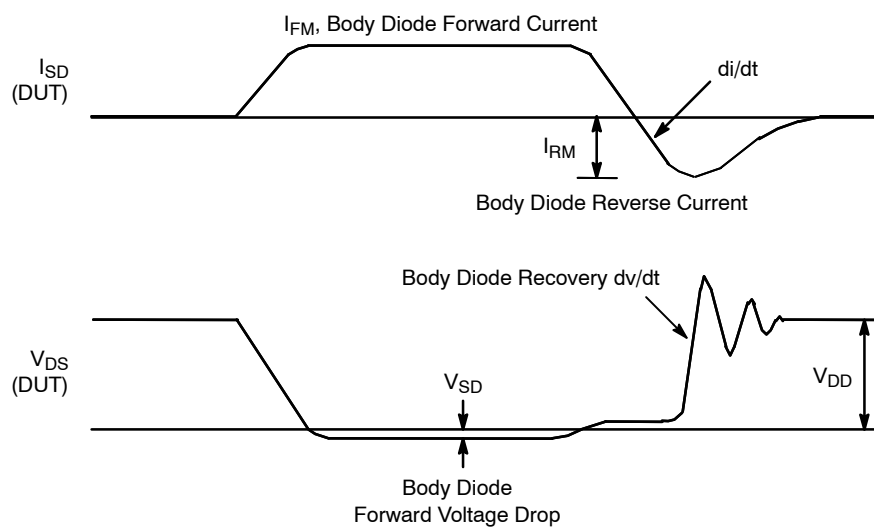
The diagram shows a switching circuit. A MOSFET labeled "DUT" has its gate connected to a driver MOSFET. The driver MOSFET's gate is driven by a square wave pulse V_{GS} through a resistor R_G . The driver MOSFET is labeled "Same Type as DUT". The drain of the driver MOSFET is connected to the gate of the DUT MOSFET. The source of the driver MOSFET is connected to ground. The drain of the DUT MOSFET is connected to a load inductor L and a DC supply V_{DD} . The source of the DUT MOSFET is connected to ground. The voltage across the DUT is labeled V_{DS} and the current through it is labeled I_{SD} . The circuit is used to study the switching behavior of the DUT.

– dv/dt controlled by R_G
– I_{SD} controlled by pulse period

V_{GS}
(Driver)

$D = \frac{\text{Gate Pulse Width}}{\text{Gate Pulse Period}}$

10 V

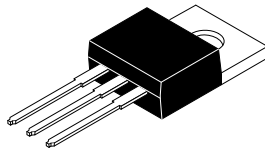


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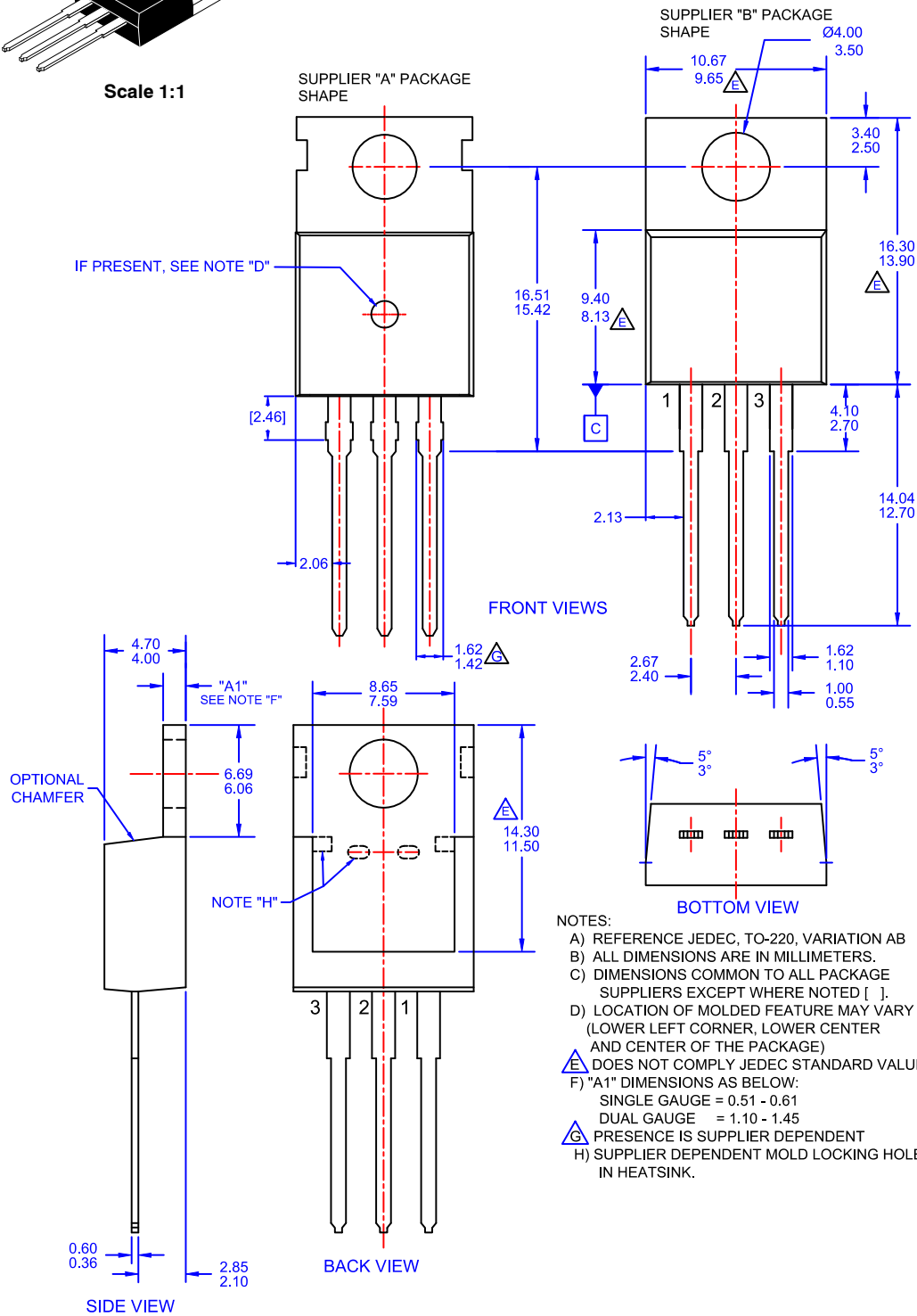
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Scale 1:1

TO-220-3LD CASE 340AT ISSUE A

DATE 03 OCT 2017



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